

ZXTN25100DZ

100V NPN high gain transistor in SOT89

Summary

$BV_{CEX} > 180V$

$BV_{CEO} > 100V$

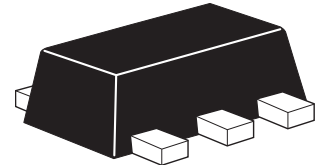
$BV_{ECO} > 6V$

$I_{C(cont)} = 2.5A$

$V_{CE(sat)} < 100mV @ 1A$

$R_{CE(sat)} = 80m\Omega$

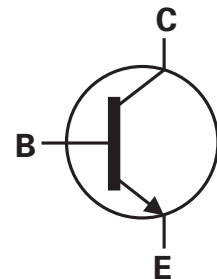
$P_D = 2.4W$



Complementary part number ZXTP25100CZ

Description

Packaged in the SOT89 outline this new low saturation NPN transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions.



Features

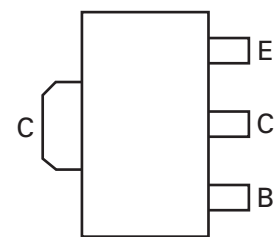
- High power dissipation SOT89 package
- High gain
- Low saturation voltage
- 180V forward blocking voltage
- 6V reverse blocking voltage

Applications

- PSU start up switch
- DC - DC converters
- Motor drive
- Relay, lamp and solenoid drive

Ordering information

| Device | Reel size (inches) | Tape width (mm) | Quantity per reel |
|---------------|--------------------|-----------------|-------------------|
| ZXTN25100DZTA | 7 | 12 | 1000 |



Pinout - top view

Device marking

1K9

ZXTN25100DZ

Absolute maximum ratings

| Parameter | Symbol | Limit | Unit |
|---|----------------|-------------|-------|
| Collector-Base voltage | V_{CBO} | 180 | V |
| Collector-Emitter voltage (forward blocking) | V_{CEX} | 180 | V |
| Collector-Emitter voltage | V_{CEO} | 100 | V |
| Emitter-Collector voltage (reverse blocking) | V_{ECO} | 6 | V |
| Emitter-Base voltage | V_{EBO} | 7 | V |
| Continuous Collector current ^(c) | I_C | 2.5 | A |
| Base current | I_B | 1 | A |
| Peak pulse current | I_{CM} | 3.5 | A |
| Power dissipation at $T_A = 25^\circ\text{C}^{(a)}$ | P_D | 1.1 | W |
| Linear derating factor | | 8.8 | mW/°C |
| Power dissipation at $T_A = 25^\circ\text{C}^{(b)}$ | P_D | 1.8 | W |
| Linear derating factor | | 14.4 | mW/°C |
| Power dissipation at $T_A = 25^\circ\text{C}^{(c)}$ | P_D | 2.4 | W |
| Linear derating factor | | 19.2 | mW/°C |
| Power dissipation at $T_A = 25^\circ\text{C}^{(d)}$ | P_D | 4.46 | W |
| Linear derating factor | | 35.7 | mW/°C |
| Power dissipation at $T_C = 25^\circ\text{C}^{(e)}$ | P_D | 19.2 | W |
| Linear derating factor | | 153 | mW/°C |
| Operating and storage temperature range | T_j, T_{stg} | -55 to +150 | °C |

Thermal resistance

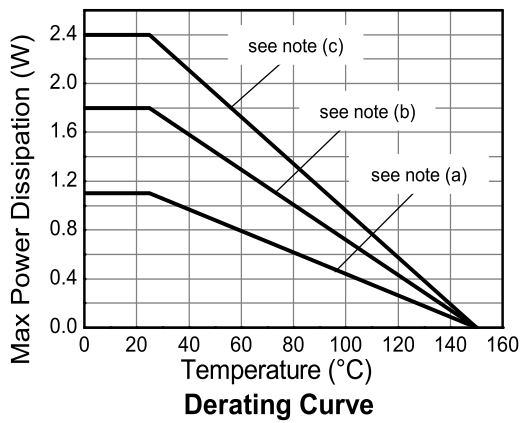
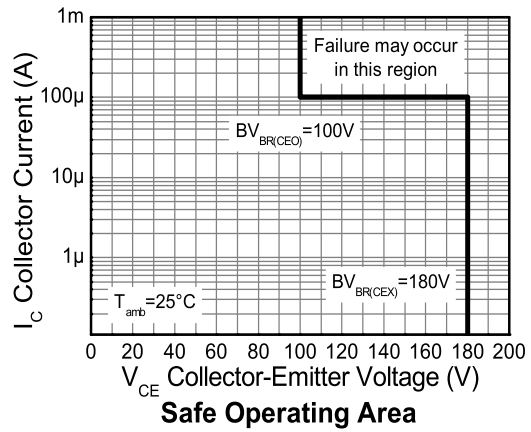
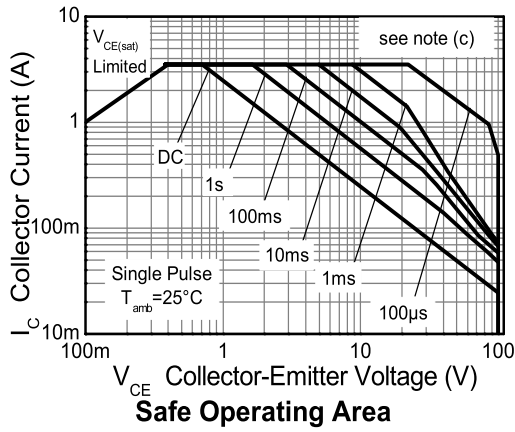
| Parameter | Symbol | Limit | Unit |
|------------------------------------|-----------------|-------|------|
| Junction to ambient ^(a) | $R_{\theta JA}$ | 117 | °C/W |
| Junction to ambient ^(b) | $R_{\theta JA}$ | 68 | °C/W |
| Junction to ambient ^(c) | $R_{\theta JA}$ | 51 | °C/W |
| Junction to ambient ^(d) | $R_{\theta JA}$ | 28 | °C/W |
| Junction to case ^(e) | $R_{\theta JC}$ | 7.95 | °C/W |

NOTES:

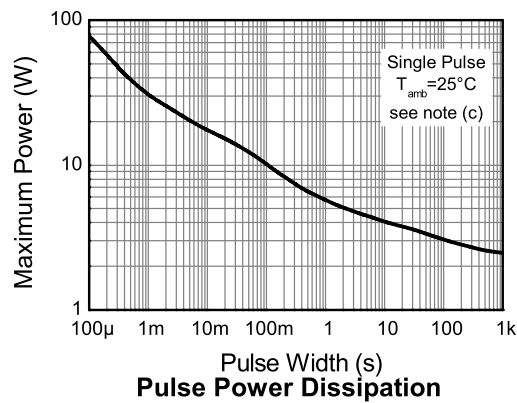
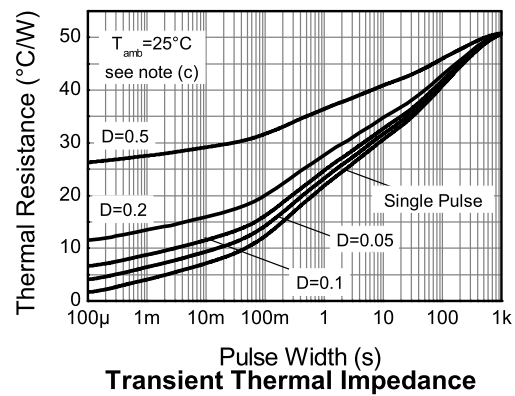
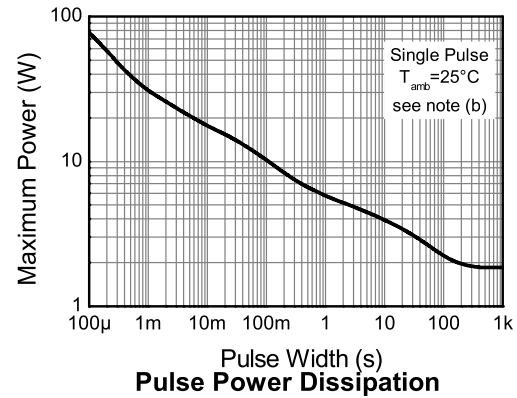
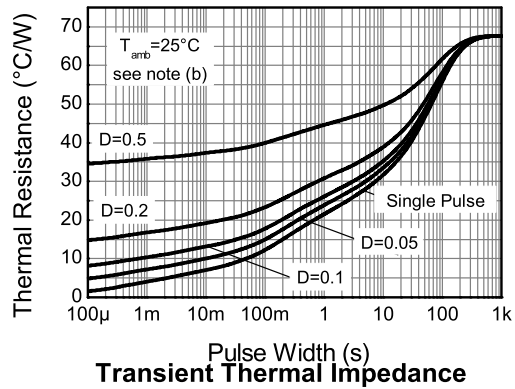
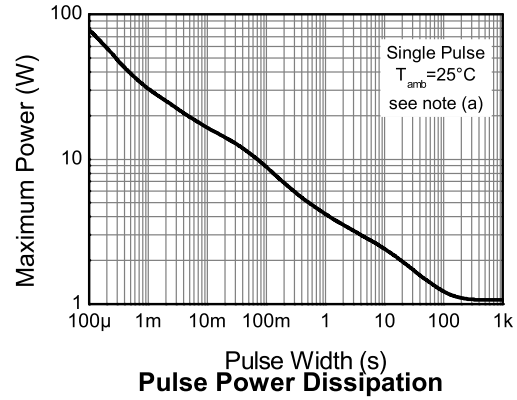
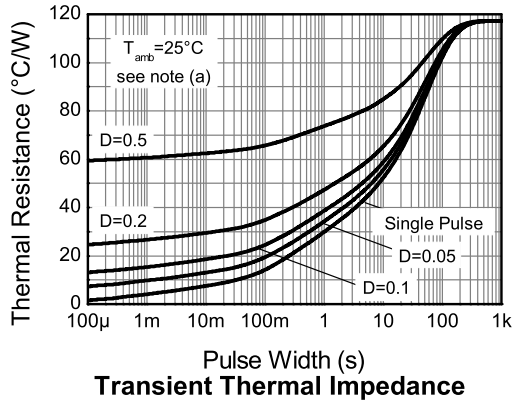
- (a) For a device surface mounted on 15mm x 15mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (b) Mounted on 25mm x 25mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (c) Mounted on 50mm x 50mm x 0.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.
- (d) As (c) above measured at $t < 5$ seconds.
- (e) Junction to case (collector tab). Typical

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Thermal characteristics



Thermal characteristics



ZXTN25100DZ

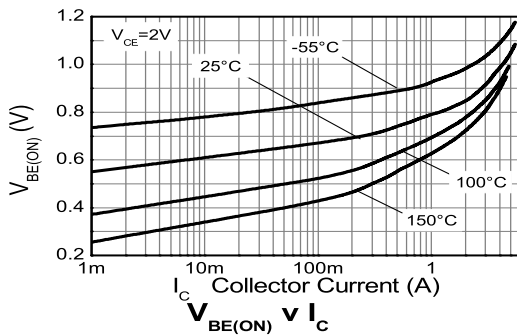
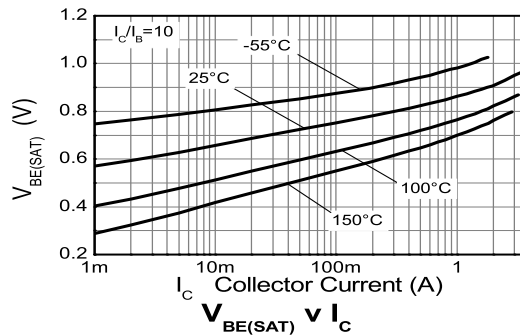
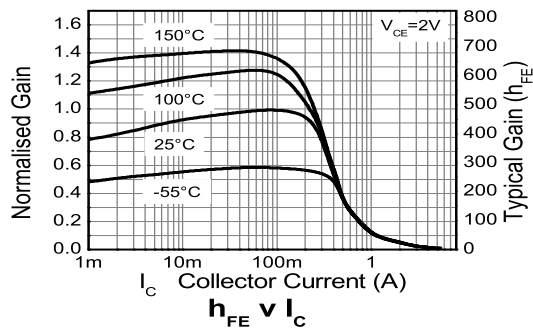
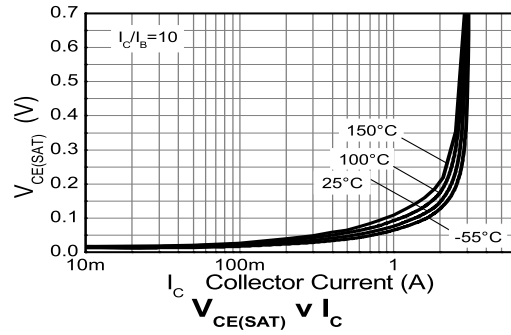
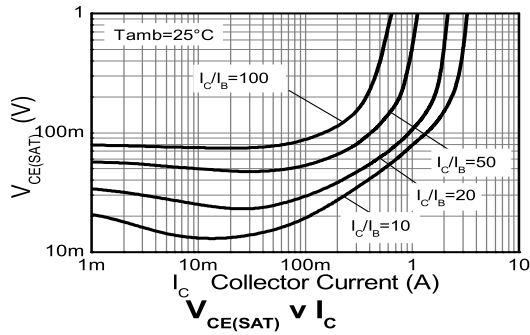
Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|--|---------------|------------------|------------------------|-------------------|---------------------|--|
| Collector-Base breakdown voltage | BV_{CBO} | 180 | 220 | | V | $I_C = 100\mu\text{A}$ |
| Collector-Emitter breakdown voltage (forward blocking) | BV_{CEX} | 180 | 220 | | V | $I_C = 100\mu\text{A}$, $R_{BE} < 1\text{k}\Omega$ or $-1\text{V} > V_{BE} > 0.25\text{V}$ |
| Collector-Emitter breakdown voltage | BV_{CEO} | 100 | 130 | | V | $I_C = 10\text{mA}^{(*)}$ |
| Emitter-Collector breakdown voltage (reverse blocking) | BV_{ECX} | 6 | 8.2 | | V | $I_E = 100\mu\text{A}$, $R_{BC} < 1\text{k}\Omega$ or $0.25\text{V} > V_{BC} > -0.25\text{V}$ |
| Emitter-Collector breakdown voltage (reverse blocking) | BV_{ECO} | 6 | 8.7 | | V | $I_E = 100\mu\text{A}$ |
| Emitter-Base breakdown voltage | BV_{EBO} | 7 | 8.3 | | V | $I_E = 100\mu\text{A}$ |
| Collector-Base cut-off current | I_{CBO} | | <1 | 50 0.5 | nA μA | $V_{CB} = 180\text{V}$ $V_{CB} = 180\text{V}$, $T_{amb} = 100^{\circ}\text{C}$ |
| Collector-Emitter cut-off current | I_{CEX} | | | 100 | nA | $V_{CE} = 100\text{V}$, $R_{BE} < 1\text{k}\Omega$ or $-1\text{V} < V_{BE} < 0.25\text{V}$ |
| Emitter cut-off current | I_{EBO} | | <1 | 50 | nA | $V_{EB} = 5.6\text{V}$ |
| Collector-Emitter saturation voltage | $V_{CE(sat)}$ | | 120 80 220 | 170 100 345 | mV mV mV | $I_C = 0.5\text{A}$, $I_B = 10\text{mA}^{(*)}$ $I_C = 1\text{A}$, $I_B = 100\text{mA}^{(*)}$ $I_C = 2.5\text{A}$, $I_B = 250\text{mA}^{(*)}$ |
| Base-Emitter saturation voltage | $V_{BE(sat)}$ | | 935 | 1000 | mV | $I_C = 2.5\text{A}$, $I_B = 250\text{mA}^{(*)}$ |
| Base-Emitter turn-on voltage | $V_{BE(on)}$ | | 890 | 950 | mV | $I_C = 2.5\text{A}$, $V_{CE} = 2\text{V}^{(*)}$ |
| Static forward current transfer ratio | h_{FE} | 300 120 40 | 450 170 60 20 | 900 | | $I_C = 10\text{mA}$, $V_{CE} = 2\text{V}^{(*)}$ $I_C = 0.5\text{A}$, $V_{CE} = 2\text{V}^{(*)}$ $I_C = 1\text{A}$, $V_{CE} = 2\text{V}^{(*)}$ $I_C = 2.5\text{A}$, $V_{CE} = 2\text{V}^{(*)}$ |
| Transition frequency | f_T | | 175 | | MHz | $I_C = 50\text{mA}$, $V_{CE} = 10\text{V}$ $f = 100\text{MHz}$ |
| Input capacitance | C_{ibo} | | 154 | 250 | pF | $V_{EB} = 0.5\text{V}$, $f = 1\text{MHz}^{(*)}$ |
| Output capacitance | C_{obo} | | 8.7 | 15 | pF | $V_{CB} = 10\text{V}$, $f = 1\text{MHz}^{(*)}$ |
| Delay time | t_d | | 16.4 | | ns | $I_C = 500\text{mA}$, $V_{CC} = 10\text{V}$, $I_{B1} = -I_{B2} = 50\text{mA}$ |
| Rise time | t_r | | 115 | | ns | |
| Storage time | t_s | | 763 | | ns | |
| Fall time | t_f | | 158 | | ns | |

NOTES:

(*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

Typical characteristics



ZXTN25100DZ

Package outline - SOT89



| DIM | Millimeters | | Inches | | DIM | Millimeters | | Inches | |
|-----|-------------|------|--------|-------|-----|-------------|------|-----------|-------|
| | Min | Max | Min | Max | | Min | Max | Min | Max |
| A | 1.40 | 1.60 | 0.550 | 0.630 | E | 2.29 | 2.60 | 0.090 | 0.102 |
| B | 0.44 | 0.56 | 0.017 | 0.022 | E1 | 2.13 | 2.29 | 0.084 | 0.090 |
| B1 | 0.36 | 0.48 | 0.014 | 0.019 | e | 1.50 BSC | | 0.059 BSC | |
| C | 0.35 | 0.44 | 0.014 | 0.017 | e1 | 3.00 BSC | | 0.118 BSC | |
| D | 4.40 | 4.60 | 0.173 | 0.181 | H | 3.94 | 4.25 | 0.155 | 0.167 |
| D1 | 1.52 | 1.83 | 0.064 | 0.072 | L | 0.89 | 1.20 | 0.035 | 0.047 |

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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| | |
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| | |
|-----------------------|---|
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